Lasse Vines

List of Publications by Year
in descending order

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184	2,598	279487	288905
papers	citations	23 h-index	40 g-index

190	190	190	2659
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Formation of carbon interstitial-related defect levels by thermal injection of carbon into n-type 4H-SiC. Journal of Applied Physics, 2022, 131, .	1.1	7
2	Radiation-induced defect accumulation and annealing in Si-implanted gallium oxide. Journal of Applied Physics, 2022, 131, .	1.1	17
3	Influence of heat treatments in H2 and Ar on the E1 center in Î²-Ga2O3. Journal of Applied Physics, 2022, 131, .	1.1	11
4	Gettering in PolySi/SiO_x Passivating Contacts Enables Si-Based Tandem Solar Cells with High Thermal and Contamination Resilience. ACS Applied Materials & Interfaces, 2022, 14, 14342-14358.	4.0	3
5	Multistability of isolated and hydrogenated Gaâ€“O divacancies in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>Î²</mml:mi><mml:mo>â¯</mml:mo><mml:msub><mml:mrow><mml:mathvariant="normal">O</mml:mi></mml:mrow><mml:mn>3</mml:mn></mml:msub></mml:math>. Physical Review Materials, 2021, 5, .	0.9	28
6	Phosphorus implantation into 4H-SiC at room and elevated temperature. Semiconductor Science and Technology, 2021, 36, 065002.	1.0	2
7	Interplay of vacancies, hydrogen, and electrical compensation in irradiated and annealed n-type Î²-Ga2O3. Journal of Applied Physics, 2021, 129, .	1.1	24
8	ZnSnN₂ in Real Space and kâ€Space: Lattice Constants, Dislocation Density, and Optical Band Gap. Advanced Optical Materials, 2021, 9, 2100015.	3.6	10
9	Manipulating Singleâ€Photon Emission from Point Defects in Diamond and Silicon Carbide. Advanced Quantum Technologies, 2021, 4, 2100003.	1.8	25
10	On the permittivity of titanium dioxide. Scientific Reports, 2021, 11, 12443.	1.6	28
11	Deep level study of chlorine-based dry etched Î²â€‰â¯â€‰Ga2O3. Journal of Applied Physics, 2021, 130, .	1.1	8
12	Resolving Jahn-Teller induced vibronic fine structure of silicon vacancy quantum emission in silicon carbide. Physical Review B, 2021, 104, .	1.1	2
13	Increased dephasing length in heavily doped GaAs. New Journal of Physics, 2021, 23, 083034.	1.2	1
14	Influence from the electronic shell structure on the range distribution during channeling of 40â€“300â€‰keV ions in 4H-SiC. Journal of Applied Physics, 2021, 130, .	1.1	8
15	Fermi level controlled point defect balance in ion irradiated indium oxide. Journal of Applied Physics, 2021, 130, 085703.	1.1	4
16	Formation and functionalization of Ge-nanoparticles in ZnO. Nanotechnology, 2021, 32, 505707.	1.3	2
17	Electrically-active defects in reduced and hydrogenated rutile TiO2. Semiconductor Science and Technology, 2021, 36, 014006.	1.0	1
18	Dominant hydrogen complex in natural anatase TiO2. Journal of Applied Physics, 2021, 130, 145701.	1.1	3

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19	Activation energy of silicon diffusion in gallium oxide: Roles of the mediating defects charge states and phase modification. Applied Physics Letters, 2021, 119, .	1.5	6
20	Optical signatures of single ion tracks in ZnO. Nanoscale Advances, 2020, 2, 724-733.	2.2	6
21	Lateral straggling of implanted aluminum in 4H-SiC. Applied Physics Letters, 2020, 116, .	1.5	13
22	Monolithic thin-film chalcogenideâ€“silicon tandem solar cells enabled by a diffusion barrier. Solar Energy Materials and Solar Cells, 2020, 207, 110334.	3.0	34
23	Spatially Resolved Diffusion of Aluminum in 4H-SiC During Postimplantation Annealing. IEEE Transactions on Electron Devices, 2020, 67, 4360-4365.	1.6	6
24	Donors and polaronic absorption in rutile TiO2 single crystals. Journal of Applied Physics, 2020, 128, 145701.	1.1	6
25	Strain Modulation of Si Vacancy Emission from SiC Micro- and Nanoparticles. Nano Letters, 2020, 20, 8689-8695.	4.5	11
26	High electron mobility single-crystalline ZnSnN₂ on ZnO (0001) substrates. CrystEngComm, 2020, 22, 6268-6274.	1.3	13
27	Persistent Double-Layer Formation in Kesterite Solar Cells: A Critical Review. ACS Applied Materials & Interfaces, 2020, 12, 39405-39424.	4.0	35
28	Influence of Carbon Cap on Self-Diffusion in Silicon Carbide. Crystals, 2020, 10, 752.	1.0	2
29	Muon Interaction with Negative- <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>U</mml:mi></mml:math> and High-Spin-State Defects: Differentiating Between <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mrow><mml:mi mathvariant="normal">C</mml:mi></mml:mrow></mml:mrow></mml:math> and <mml:math	1.5	7
30	Conversion pathways of primary defects by annealing in proton-irradiated <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math> -type <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:mrow></mml:m -SiC. Physical Review B, 2020, 102, .	1.1	36
31	Fabrication and characterization of Schottky barrier diodes on rutile TiO₂. Materials Research Express, 2020, 7, 065903.	0.8	5
32	Combining steady-state photo-capacitance spectra with first-principles calculations: the case of Fe and Ti in Î²-Ga2O3. New Journal of Physics, 2020, 22, 063033.	1.2	10
33	Ti- and Fe-related charge transition levels in Î²â^'Ga2O3. Applied Physics Letters, 2020, 116, .	1.5	37
34	Transition-Metal Oxides for Kesterite Solar Cells Developed on Transparent Substrates. ACS Applied Materials & Interfaces, 2020, 12, 33656-33669.	4.0	29
35	Influence of hydrogen implantation on emission from the silicon vacancy in 4H-SiC. Journal of Applied Physics, 2020, 127, .	1.1	14
36	Formation of N₂ bubbles along grain boundaries in (ZnO)_{1â^'x}(GaN)_x: nanoscale STEM-EELS studies. Physical Chemistry Chemical Physics, 2020, 22, 3779-3783.	1.3	6

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37	Self-trapped hole and impurity-related broad luminescence in Î²-Ga2O3. Journal of Applied Physics, 2020, 127, .	1.1	87
38	Dynamic Impurity Redistributions in Kesterite Absorbers. Physica Status Solidi (B): Basic Research, 2020, 257, 2000062.	0.7	4
39	Nitride-Based Interfacial Layers for Monolithic Tandem Integration of New Solar Energy Materials on Si: The Case of CZTS. ACS Applied Energy Materials, 2020, 3, 4600-4609.	2.5	19
40	Anisotropic and trap-limited diffusion of hydrogen/deuterium in monoclinic gallium oxide single crystals. Applied Physics Letters, 2020, 117, .	1.5	16
41	Formation and control of the E2âˆ— center in implanted Î²-Ga 2 O 3 by reverse-bias and zero-bias annealing. Journal Physics D: Applied Physics, 2020, 53, 464001.	1.3	18
42	Experimental exploration of the amphoteric defect model by cryogenic ion irradiation of a range of wide band gap oxide materials. Journal of Physics Condensed Matter, 2020, 32, 415704.	0.7	7
43	First-principles calculations of Stark shifts of electronic transitions for defects in semiconductors: the Si vacancy in 4H-SiC. Journal of Physics Condensed Matter, 2020, 33, 075502.	0.7	5
44	Primary intrinsic defects and their charge transition levels in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>Î²</mml:mi><mml:mtext>â€“</mml:mtext><mml:mi>Ga</mml:mi><mml:msub><mml:mi /><mml:mn>2</mml:mn></mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>. Physical Review Materials, 2020, 4, .	0.9	21
45	Generation and metastability of deep level states in Î²-Ga2O3 exposed to reverse bias at elevated temperatures. Journal of Applied Physics, 2019, 125, 185706.	1.1	13
46	Role of Nitrogen in Defect Evolution in Zinc Oxide: STEMâ€“EELS Nanoscale Investigations. Journal of Physical Chemistry Letters, 2019, 10, 4725-4730.	2.1	12
47	Strong Interplay between Sodium and Oxygen in Kesterite Absorbers: Complex Formation, Incorporation, and Tailoring Depth Distributions. Advanced Energy Materials, 2019, 9, 1900740.	10.2	20
48	Anisotropic and plane-selective migration of the carbon vacancy in SiC: Theory and experiment. Physical Review B, 2019, 100, .	1.1	20
49	Nanoscale n++-p junction formation in GeOI probed by tip-enhanced Raman spectroscopy and conductive atomic force microscopy. Journal of Applied Physics, 2019, 125, 245703.	1.1	5
50	Intentional and unintentional channeling during implantation of ⁵¹V ions into 4H-SiC. Semiconductor Science and Technology, 2019, 34, 115006.	1.0	10
51	Role of intrinsic and extrinsic defects in H implanted hydrothermally grown ZnO. Journal of Applied Physics, 2019, 126, 125707.	1.1	10
52	Broad luminescence from donor-complexed <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">Li</mml:mi><mml:mtext>Zn</mml:mtext></mml:msub></mml:math> and <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">Na</mml:mi><mml:mtext>Zn</mml:mtext></mml:msub></mml:math> acceptors in ZnO. Physical Review B, 2019, 100, .	1.1	8
53	Evidence of defect band mechanism responsible for band gap evolution in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow><mml:mo>(</mml:mo><mml:mi>ZnO</mml:mi><mml:mi> alloys. Physical Review B, 2019, 100, .	1.1	14
54	Bulk In2O3 crystals grown by chemical vapour transport: a combination of XPS and DFT studies. Journal of Materials Science: Materials in Electronics, 2019, 30, 18753-18758.	1.1	12

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55	Negative-<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>U</mml:mi></mml:math>and polaronic behavior of the Zn-O divacancy in ZnO. Physical Review B, 2019, 99, .	1.1	13
56	Influence of Oxygen Pressure on Growth of Si-Doped Î²-(Al_xGa<sub>1 â^') Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 707 Deposition. ECS Journal of Solid State Science and Technology, 2019, 8, Q3217-Q3220.	0.9	18
57	Effects of Substrate and Postâ€Deposition Annealing on Structural and Optical Properties of (ZnO)_{1â^'x}(GaN)_x Films. Physica Status Solidi (B): Basic Research, 2019, 256, 1800529.	0.7	5
58	ZnCr2O4 Inclusions in ZnO Matrix Investigated by Probe-Corrected STEM-EELS. Materials, 2019, 12, 888.	1.3	4
59	Highly Correlated Hydride Ion Tracer Diffusion in SrTiO_{3â€“x}H_x Oxyhydrides. Journal of the American Chemical Society, 2019, 141, 4653-4659.	6.6	20
60	Defect annealing kinetics in ZnO implanted with Zn substituting elements: Zn interstitials and Li redistribution. Journal of Applied Physics, 2019, 125, .	1.1	8
61	Structural and optical properties of individual Zn2GeO4 particles embedded in ZnO. Nanotechnology, 2019, 30, 225702.	1.3	3
62	Influence of a thin amorphous surface layer on de-channeling during aluminum implantation at different temperatures into 4H-SiC. Applied Physics A: Materials Science and Processing, 2019, 125, 1.	1.1	2
63	Electrical charge state identification and control for the silicon vacancy in 4H-SiC. Npj Quantum Information, 2019, 5, .	2.8	54
64	Formation and Characterization of Shallow Junctions in GaAs Made by Ion Implantation and msâ€Range Flash Lamp Annealing. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800618.	0.8	3
65	Diffusion of indium in single crystal zinc oxide: a comparison between group III donors. Semiconductor Science and Technology, 2019, 34, 025011.	1.0	4
66	Impact of proton irradiation on conductivity and deep level defects in Î²-Ga2O3. APL Materials, 2019, 7, .	2.2	143
67	Bandgap bowing in crystalline (ZnO)_{1â^'x}(GaN)_x thin films; influence of composition and structural properties. Semiconductor Science and Technology, 2019, 34, 015001.	1.0	7
68	The temperature-dependency of the optical band gap of ZnO measured by electron energy-loss spectroscopy in a scanning transmission electron microscope. Journal of Applied Physics, 2018, 123, .	1.1	10
69	Iron and intrinsic deep level states in Ga2O3. Applied Physics Letters, 2018, 112, .	1.5	196
70	Gallium diffusion in zinc oxide via the paired dopant-vacancy mechanism. Journal of Applied Physics, 2018, 123, .	1.1	13
71	Influence of annealing atmosphere on formation of electrically-active defects in rutile TiO2. Journal of Applied Physics, 2018, 123, 161572.	1.1	6
72	Electrical conductivity of In₂O₃and Ga₂O₃after low temperature ion irradiation; implications for instrinsic defect formation and charge neutrality level. Journal of Physics Condensed Matter, 2018, 30, 025502.	0.7	15

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73	The interaction between lithium acceptors and gallium donors in zinc oxide. Journal of Applied Physics, 2018, 124, 245702.	1.1	1
74	Influence of Fermi level position on vacancy-assisted diffusion of aluminum in zinc oxide. Physical Review B, 2018, 98, .	1.1	7
75	Low temperature incorporation of selenium in Cu2ZnSnS4: Diffusion and nucleation. Thin Solid Films, 2018, 665, 159-163.	0.8	5
76	Direct observation of conduction band plasmons and the related Burstein-Moss shift in highly doped semiconductors: A STEM-EELS study of Ga-doped ZnO. Physical Review B, 2018, 98, .	1.1	19
77	Phase stability and strain accumulation in CdO as a function of Cd/O supply during MOVPE synthesis. Superlattices and Microstructures, 2018, 120, 569-577.	1.4	0
78	Selenium Inclusion in Cu₂ZnSn(S,Se)₄Solar Cell Absorber Precursors for Optimized Grain Growth. IEEE Journal of Photovoltaics, 2018, 8, 1132-1141.	1.5	6
79	Practical limitations to selenium annealing of compound co-sputtered Cu 2 ZnSnS 4 as a route to achieving sulfur-selenium graded solar cell absorbers. Thin Solid Films, 2017, 623, 110-115.	0.8	14
80	Comparison of the structural properties of Zn-face and O-face single crystal homoepitaxial ZnO epilayers grown by RF-magnetron sputtering. Journal of Applied Physics, 2017, 121, .	1.1	5
81	Limitation of Na-H codoping in achieving device-quality p-type ZnO. Materials Science in Semiconductor Processing, 2017, 69, 28-31.	1.9	6
82	Subsurface damage in polishingâ€“annealing processed ZnO substrates. Materials Science in Semiconductor Processing, 2017, 69, 19-22.	1.9	4
83	Dopant incorporation in Al 0.9 Ga 0.1 As 0.06 Sb 0.94 grown by molecular beam epitaxy. Journal of Crystal Growth, 2017, 463, 116-122.	0.7	2
84	Formation of Zn- and O- vacancy clusters in ZnO through deuterium annealing. Materials Science in Semiconductor Processing, 2017, 69, 23-27.	1.9	14
85	Diffusivity of the double negatively charged mono-vacancy in silicon. Journal of Physics Condensed Matter, 2017, 29, 205501.	0.7	0
86	Formation and evolution of E3 centers in hydrothermally grown zinc oxide. Materials Science in Semiconductor Processing, 2017, 69, 13-18.	1.9	4
87	Bifacial Kesterite Solar Cells on FTO Substrates. ACS Sustainable Chemistry and Engineering, 2017, 5, 11516-11524.	3.2	45
88	On the recombination centers of iron-gallium pairs in Ga-doped silicon. Journal of Applied Physics, 2017, 122, .	1.1	20
89	Photoinduced small polarons bound to hydrogen defects in rutile <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>TiO</mml:mi><mml:mn>2</mml:mn></mml:msub></m Physical Review B, 2017, 96, .	1.1	6
90	Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. ECS Journal of Solid State Science and Technology, 2017, 6, P741-P745.	0.9	1

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91	(Invited) Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. ECS Transactions, 2017, 80, 107-115.	0.3	1
92	Complementary study of the photoluminescence and electrical properties of ZnO films grown on 4H-SiC substrates. Journal of Luminescence, 2017, 181, 374-381.	1.5	6
93	Mixed sulfur and selenium annealing study of compound-sputtered bilayer CU2ZnSnS4 / Cu2ZnSnSe4 precursors. , 2017, , .		0
94	Secondary ion mass spectrometry as a tool to study selenium gradient in Cu ₂ ZnSn(S,Se) ₄. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, 1600187.	0.8	5
95	Zn precipitation and Li depletion in Zn implanted ZnO. Applied Physics Letters, 2016, 109, 022102.	1.5	3
96	Formation and annihilation of E4 centers in ZnO: Influence of hydrogen. Journal of Applied Physics, 2016, 119, .	1.1	13
97	The effect of millisecond flash lamp annealing on electrical and structural properties of ZnO:Al/Si structures. Journal of Applied Physics, 2016, 119, 185305.	1.1	10
98	Cu<inf>2</inf>ZnSn(S, Se)<inf>4</inf> solar cell absorbers from diffusion of selenium into annealed Cu<inf>2</inf>ZnSnS<inf>4</inf> absorbers. , 2016, , .		0
99	Silver migration and trapping in ion implanted ZnO single crystals. Journal of Applied Physics, 2016, 119, .	1.1	12
100	Evolution kinetics of elementary point defects in ZnO implanted with low fluences of helium at cryogenic temperature. Physical Review B, 2016, 94, .	1.1	14
101	Enhancement of carrier mobility in thin Ge layer by Sn co-doping. Semiconductor Science and Technology, 2016, 31, 105012.	1.0	7
102	Ultra-doped n-type germanium thin films for sensing in the mid-infrared. Scientific Reports, 2016, 6, 27643.	1.6	64
103	Single-crystal TiO₂ nanowires by seed assisted thermal oxidation of Ti foil: synthesis and photocatalytic properties. RSC Advances, 2016, 6, 55490-55498.	1.7	5
104	Band-gap narrowing in Mn-doped GaAs probed by room-temperature photoluminescence. Physical Review B, 2015, 92, .	1.1	13
105	Coincident site lattice bi-crystals growthâ€"Impurity segregation towards grain boundaries. Journal of Crystal Growth, 2015, 416, 8-11.	0.7	7
106	Aluminum Migration and Intrinsic Defect Interaction in Single-Crystal Zinc Oxide. Physical Review Applied, 2015, 3, .	1.5	38
107	Equilibrium shape of nano-cavities in H implanted ZnO. Applied Physics Letters, 2015, 106, .	1.5	6
108	Hydrogen induced optically-active defects in silicon photonic nanocavities. Optics Express, 2014, 22, 8843.	1.7	7

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109	Hydrogen engineering via plasma immersion ion implantation and flash lamp annealing in silicon-based solar cell substrates. Journal of Applied Physics, 2014, 115, 064505.	1.1	14
110	The E3 center in zinc oxide: Evidence for involvement of hydrogen. Applied Physics Letters, 2014, 104, .	1.5	20
111	Formation kinetics of trivacancy-oxygen pairs in silicon. Journal of Applied Physics, 2014, 116, 124510.	1.1	3
112	Identification of Grain Boundary Segregation Mechanisms during Silicon Bi-Crystal Solidification. Materials Science Forum, 2014, 790-791, 329-334.	0.3	1
113	Effects of high temperature annealing on defects and luminescence properties in H implanted ZnO. Journal Physics D: Applied Physics, 2014, 47, 342001.	1.3	8
114	Transformation of divacancies to divacancy-oxygen pairs in p-type Czochralski-silicon; mechanism of divacancy diffusion. Journal of Applied Physics, 2014, 115, 034514.	1.1	13
115	Zinc-Vacancyâ€“Donor Complex: A Crucial Compensating Acceptor in ZnO. Physical Review Applied, 2014, 2, .	1.5	51
116	Influence of pulling rate on multicrystalline silicon ingots' properties. Journal of Crystal Growth, 2014, 386, 199-203.	0.7	9
117	Bulk Growth and Impurities. Semiconductors and Semimetals, 2013, 88, 67-104.	0.4	7
118	Intrinsic Point-Defect Balance in Self-Ion-Implanted ZnO. Physical Review Letters, 2013, 110, 015501.	2.9	28
119	Divacancy-iron complexes in silicon. Journal of Applied Physics, 2013, 113, 044503.	1.1	4
120	Impurity Sublattice Localization in ZnO Revealed by Li Marker Diffusion. Physical Review Letters, 2013, 110, 175503.	2.9	15
121	Impact of growth rate on impurities segregation at grain boundaries in silicon during Bridgman growth. Journal of Crystal Growth, 2013, 372, 180-188.	0.7	18
122	Iron related donor-like defect in zinc oxide. Applied Physics Letters, 2013, 102, .	1.5	12
123	Defect formation and thermal stability of H in high dose H implanted ZnO. Journal of Applied Physics, 2013, 114, 083111.	1.1	19
124	Phosphorus in-diffusion from a surface source by millisecond flash lamp annealing for shallow emitter solar cells. Applied Physics Letters, 2013, 102, 132108.	1.5	12
125	Anomalous Diffusion of Intrinsic Defects in K+ Implanted ZnO using Li as Tracer. Materials Research Society Symposia Proceedings, 2012, 1394, 75.	0.1	2
126	Acceptor-like deep level defects in ion-implanted ZnO. Applied Physics Letters, 2012, 100, 212106.	1.5	15

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127	Long range lateral migration of intrinsic point defects in n-type 4H-SiC. Journal of Applied Physics, 2012, 111, 103719.	1.1	3
128	Al and Si doping of sputtered ZnO thin films. IOP Conference Series: Materials Science and Engineering, 2012, 34, 012007.	0.3	7
129	Simulation and electrical characterization of Pd as Schottky contact on hydrothermally grown ZnO. Physica Scripta, 2012, T148, 014007.	1.2	0
130	Evolution of deep electronic states in ZnO during heat treatment in oxygen- and zinc-rich ambients. Applied Physics Letters, 2012, 100, 112108.	1.5	43
131	Structural and optical properties of H implanted ZnO. , 2012, , .		0
132	The work function of n-ZnO deduced from heterojunctions with Si prepared by ALD. Journal Physics D: Applied Physics, 2012, 45, 315101.	1.3	31
133	Formation of donor and acceptor states of the divacancyâ€“oxygen centre in p-type Cz-silicon. Journal of Physics Condensed Matter, 2012, 24, 435801.	0.7	10
134	Deep level transient spectroscopy on protonâ€irradiated Feâ€contaminated pâ€type silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1992-1995.	0.8	3
135	Defects in p-type Cz-silicon irradiated at elevated temperatures. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 2009-2012.	0.8	13
136	Impurity migration in bulk and thin-film ZnO. Physica Scripta, 2012, T148, 014005.	1.2	4
137	Ion implantation induced defects in ZnO. Physica B: Condensed Matter, 2012, 407, 1481-1484.	1.3	11
138	Electronic states at the interface between indium tin oxide and silicon. Journal of Applied Physics, 2011, 110, .	1.1	9
139	Self-compensation in semiconductors: The Zn vacancy in Ga-doped ZnO. Physical Review B, 2011, 84, .	1.1	169
140	Electrical Characterization of Hydrothermally Grown ZnO Annealed in Different Atmospheres. International Journal of Applied Ceramic Technology, 2011, 8, 1017-1022.	1.1	7
141	Li and OH-Li Complexes in Hydrothermally Grown Single-Crystalline ZnO. Journal of Electronic Materials, 2011, 40, 429-432.	1.0	11
142	Hydrogen-related defects in boron doped p-type silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 705-708.	0.8	3
143	Effect of the crystallinity of MOCVD-grown ZnO:N on the diffusion of impurities. Journal of Crystal Growth, 2011, 324, 243-247.	0.7	2
144	Electronic properties of n-ZnO(Al)/p-Si heterojunction prepared by dc magnetron sputtering. Thin Solid Films, 2011, 519, 5763-5766.	0.8	12

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145	Defect evolution and impurity migration in Na-implanted ZnO. Physical Review B, 2011, 84, .	1.1	28
146	Electronic properties of vacancy related defects in ZnO induced by mechanical polishing. Applied Physics Letters, 2011, 99, .	1.5	14
147	Interaction between hydrogen and the Fe-B pair in boron-doped p-type silicon. Applied Physics Letters, 2011, 99, 052106.	1.5	7
148	Composition and structure of Pd nanoclusters in SiOx thin film. Journal of Applied Physics, 2011, 109, 084329.	1.1	12
149	Hydrogen-Induced Dissociation of the Fe-B Pair in Boron-Doped P-Type Silicon. Solid State Phenomena, 2011, 178-179, 183-187.	0.3	0
150	Preferential Grain Etching of AlMgSi(Zn) Model Alloys. ECS Transactions, 2010, 25, 71-79.	0.3	6
151	Dopant incorporation in thin strained Si layers implanted with Sb. Thin Solid Films, 2010, 518, 2474-2477.	0.8	0
152	Preferential Grain Etching of AlMgSi(Zn) Model Alloys. Journal of the Electrochemical Society, 2010, 157, C424.	1.3	11
153	Lithium and electrical properties of ZnO. Journal of Applied Physics, 2010, 107, .	1.1	44
154	Defects in virgin hydrothermally grown n-type ZnO studied by temperature dependent Hall effect measurements. Journal of Applied Physics, 2009, 106, .	1.1	19
155	Transportation of Na and Li in Hydrothermally Grown ZnO. Materials Research Society Symposia Proceedings, 2009, 1201, 1.	0.1	0
156	Formation and annealing behavior of prominent point defects in MeV ion implanted n-type epitaxial Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 177-181.	1.7	1
157	Effect of high temperature treatments on defect centers and impurities in hydrothermally grown ZnO. Physica B: Condensed Matter, 2009, 404, 4386-4388.	1.3	13
158	Correlation between nitrogen and carbon incorporation into MOVPE ZnO at various oxidizing conditions. Microelectronics Journal, 2009, 40, 232-235.	1.1	9
159	Effect of spatial defect distribution on the electrical behavior of prominent vacancy point defects in swift-ion implanted Si. Physical Review B, 2009, 79, .	1.1	17
160	Interaction between Na and Li in ZnO. Applied Physics Letters, 2009, 95, 242111.	1.5	17
161	The use of nanocavities for the fabrication of ultrathin buried oxide layers. Applied Physics Letters, 2009, 94, 011903.	1.5	18
162	Defect and dopant kinetics in laser anneals of Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 154-155, 35-38.	1.7	6

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163	Formation and origin of the dominating electron trap in irradiated<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>p</mml:mi></mml:math>-type silicon. Physical Review B, 2008, 78, .	1.1	20
164	Thermal and non-thermal kinetics of defects and dopant in Si. , 2008, , .		0
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